

# RJK0354DSP

# Silicon N Channel Power MOS FET Power Switching

REJ03G1661-0101 Rev.1.01 Apr 24, 2008

# **Features**

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 5.4 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V)}$
- Pb-free

# **Outline**

RENESAS Package code: PRSP0008DD-D (Package name: SOP-8<FP-8DAV>)

8765

B 7 8 D D D D

1, 2, 3 Source
4 Gate
5, 6, 7, 8 Drain

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	16	A
Drain peak current	I <sub>D(pulse)</sub> Note1	128	A
Body-drain diode reverse drain current	I <sub>DR</sub>	16	A
Avalanche current	I <sub>AP</sub> Note 2	15	A
Avalanche energy	E <sub>AR</sub> Note 2	22.5	mJ
Channel dissipation	Pch Note3	2.0	W
Channel to ambient thermal impedance	θch-a Note3	62.5	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10s

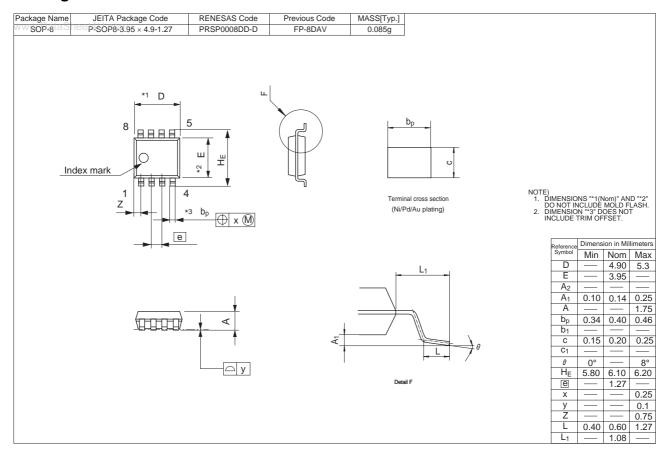
# **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	_	_	± 0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	5.4	7.0	mΩ	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	7.5	10.5	mΩ	$I_D = 8 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	_	40	_	S	$I_D = 8 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1740	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	335	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	110	_	pF	f = 1 MHz
Gate Resistance	Rg	_	4.4	_	Ω	
Total gate charge	Qg	_	12	_	nC	V <sub>DD</sub> = 10 V
Gate to source charge	Qgs	_	4.3	_	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Qgd	_	2.5	_	nC	$I_D = 8 A$
Turn-on delay time	t <sub>d(on)</sub>	_	7.4	_	ns	$V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$
Rise time	t <sub>r</sub>	_	3.6	_	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	56.4	_	ns	$R_L = 1.25 \Omega$
Fall time	t <sub>f</sub>	_	5.5	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	0.81	1.06	V	$I_F = 16 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	20	_	ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F / dt = 100 \text{ A} / \mu \text{s}$

Notes: 4. Pulse test

# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK0354DSP-00-J0	2500 pcs	Taping

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